

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Application Number	10/525,297
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2822
Examiner Name	Bac H. Au
Attorney Docket Number	070050.2717

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
	1.	4514895	5/7/1985	Nishimura, Tadashi
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	3.	5417897	5/23/1995	Asakawa, Stuart D. ; McClelland, Paul H. ; Tappon, Ellen R. ; Vandepoll, Richard R. ; Trueba, Kenneth E. ; Chen, Chien Hua
	4.	5436095	7/25/1995	Mizuno, Fumio ; Moriuchi, Noboru ; Shirai, Seiichiro ; Morita, Masayuki
	5.	5466908	11/14/1995	Hosoya, Kimio ; Teruya, Yoshihiro ; Kobayashi, Yasushi
	6.	5512494	4/30/1996	Tanabe, Hiroshi
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	12.	5736709	4/7/1998	Neiheisel, Gary L.

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	13.	6093934	7/25/2000	Yamazaki, Shunpei ; Teramoto, Satoshi ; Koyama, Jun ; Ogata, Yasushi ; Hayakawa, Masahiko ; Osame, Mitsuaki ; Ohtani, Hisashi ; Hamatani, Toshiji
	14.	6117301	9/12/2000	Freudenberger, Renate ; Zielonka, Andreas
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	23.	6388386	5/14/2002	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio

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	36.	6471772	10/29/2002	Tanaka, Koichiro

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	48.	6512634	1/28/2003	Tanaka, Koichiro

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	63.	6635932	10/21/2003	Grigoropoulos, Costas P. ; Hatano, Mutsuko ; Lee, Ming Hong ; Moon, Seung Jae
	64.	6660575	12/9/2003	Zhang, Hongyong
	65.	6667198	12/23/2003	Shimoto, Shigeyuki ; Uchikoga, Shuichi
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	68.	20040127066	7/1/2004	Jung, Yun Ho
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	71.	6770545	8/3/2004	Yang, Myoung Su
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	73.	20040169176	9/2/2004	Peterson, Paul, E. ; Stasiak, James
	74.	20040182838	9/23/2004	Das, Palash, P. ; Bolliger, Bruce, E. ; Patel, Parthiv, S. ; Klene, Brian, C. ; Melcher, Paul, C. ; Saethre, Robert, B.

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	78.	20050059265	3/17/2005	Im, James
	79.	6908835	6/21/2005	Sposili, Robert S. ; Im, James S.
	80.	20050141580	6/30/2005	Partlo, William ; Das, Palash ; Hudyma, Russell ; Thomas, Michael
	81.	20050142450	6/30/2005	Jung, Yun
	82.	20050142451	6/30/2005	You, JaeSung
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	86.	20060102901	5/18/2006	Im, James ; van der Wilt, Paul
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	88.	7091411	8/15/2006	Falk, Fritz ; Andrae, Gudrun
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	90.	20060254500	11/16/2006	Im, James ; Van Der Wilt, Paul
	91.	20070007242	1/11/2007	Im, James
	92.	20070020942	1/25/2007	Im, James
	93.	20070032096	2/8/2007	Im, James, S.
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	95.	7217605	5/15/2007	Kawasaki, Ritsuko ; Nakajima, Setsuo
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	97.	20070111349	5/17/2007	Im, James
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Exam Initial	No.	<b>OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)</b>

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	Inventor(s)	James S. Im
	Art Unit	2822
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	Attorney Docket Number	070050.2717

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